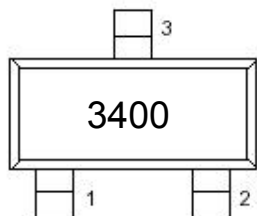


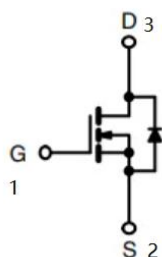
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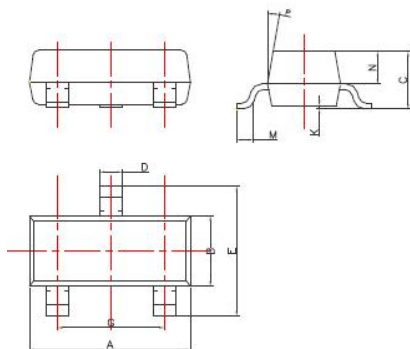
Marking: 3400



Top view

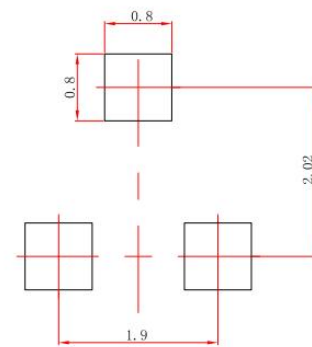


SOT-23 Dimension



DIM	Millimeters
A	2.85~3.04
B	1.30±0.10
C	1.00±0.10
D	0.45±0.05
E	2.25~2.55
G	1.90±0.1
K	0.00-0.10
M	0.20 MIN
N	0.60±0.10
P	7±2°

SOT-23 Suggested Layout



mm(±0.05mm)

MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	30	Vdc
Gate-Source Voltage	V _{GS}	±12	Vdc
Drain Current—Continuous	I _D	5.8	Adc
Peak Drain Current	I _{DM} ¹	20	Adc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation TA=25°C	P _D	450	mW
Thermal Resistance from Junction to Ambient	R _{θJA}	278	°C/W
Junction and Storage Temperature	T _J , T _{stg}	150 ¹ , -55 to +150	°C

1. Repetitive Rating : Pulse width limited by maximum junction temperature

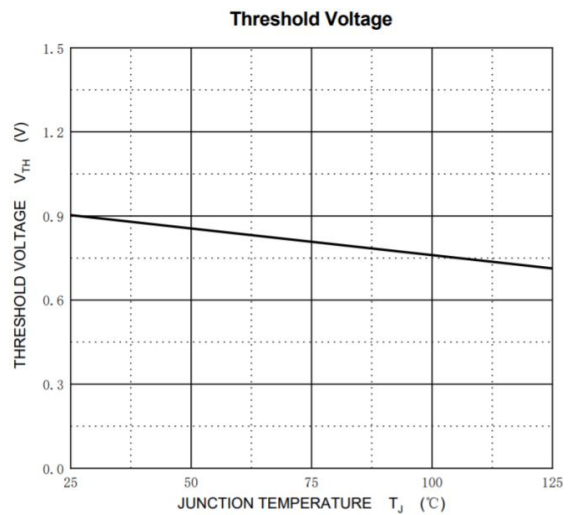
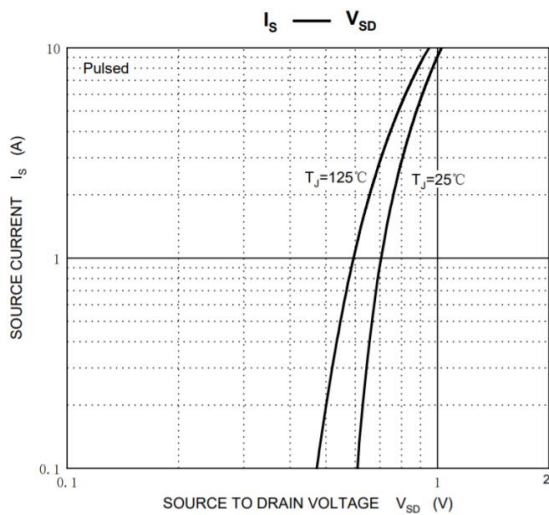
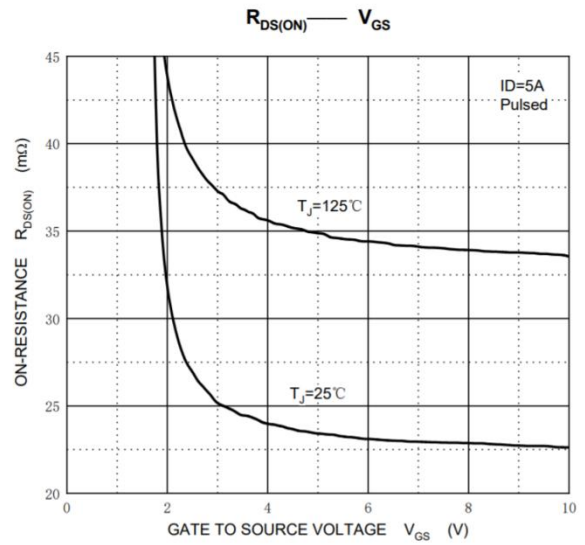
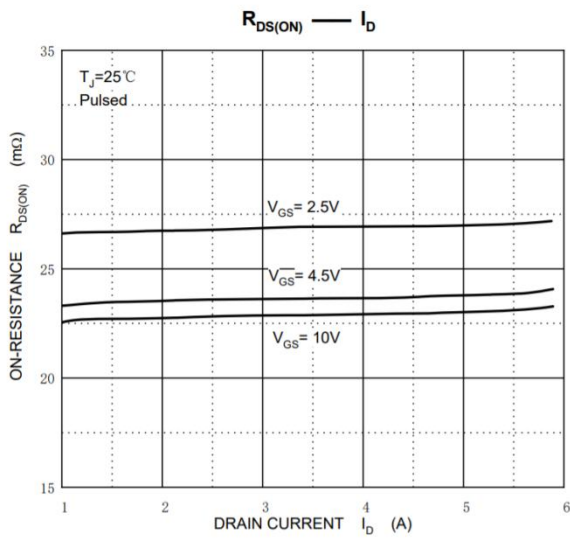
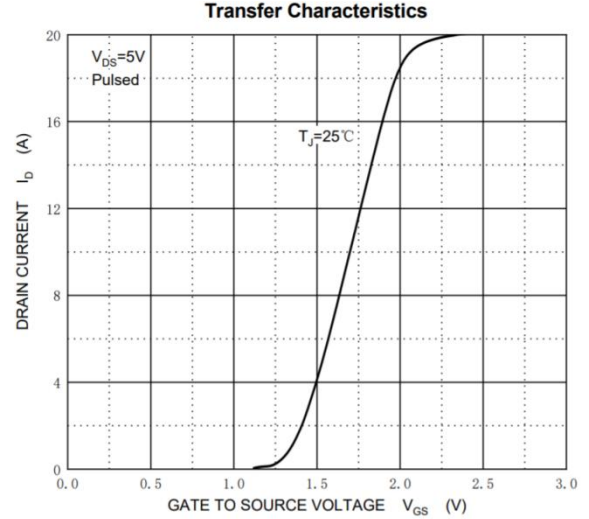
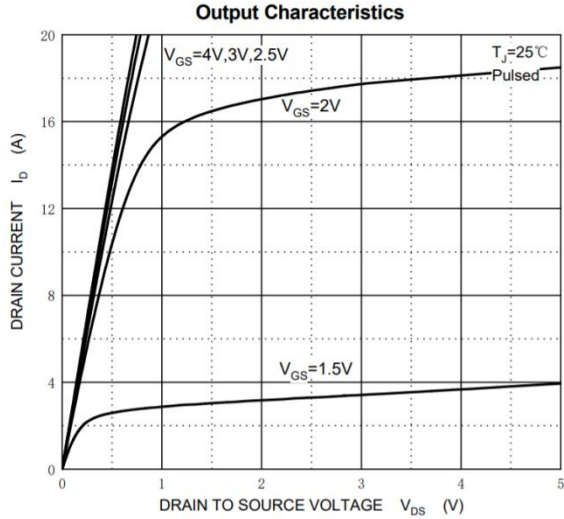
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Type	Max	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V	-	-	1.0	μA
Gate-Body Leakage Current, Forward	I _{GSS}	V _{GS} =±12V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.70	0.95	1.2	V
Static Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =5.8A	-	22	35	mΩ
		V _{GS} =4.5V, I _D =5.0A	-	25	40	
		V _{GS} =2.5V, I _D =4.0A	-	37	52	
Forward Transconductance	g _{fs}	V _{DS} =5V, I _D =5.0A	8	-	-	S
Diode Forward On-Voltage	V _{SD}	V _{GS} =0V, I _S =5.0A	-	-	1.2	V
Turn-On Delay Time	t _{d(on)}	VDD = 10V, VDS=15V, ID=5A, RL = 2.7Ω, RGEN = 3Ω	-	4.4	-	ns
Turn-On Time	t _r		-	28.2	-	
Turn-Off Delay Time	t _{d(off)}		-	16.2	-	
Turn-On Fall Time	t _f		-	26	-	
Input Capacitance	C _{iss}	VDS = 15V, VGS = 0V, f = 1.0 MHz	-	630	-	pF
Output Capacitance	C _{oss}		-	55	-	
Reverse Transfer Capacitance	C _{rss}		-	71	-	
Total Gate Charge	Q _G	VDS = 10V, ID = 5A, VGS=6V	-	17.25	-	nC
Gate to source charge	Q _{GS}		-	2.1	-	
Gate to drain charge	Q _{GD}		-	2	-	

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Typical Performance Characteristics



Note: Specifications are subject to change without notice. For more detail and update, please visit our website.